ECEN325 Ref Sheet © Josh Wright April 3, 2017

Metric Prefixes

peta	P	10^{15}	1 000 000 000 000 000
tera	T	10^{12}	1 000 000 000 000
giga	G	10^{9}	1 000 000 000
mega	M	10^{6}	1 000 000
kilo	k	10^{3}	1 000
hecto	h	10^{2}	100
deca	da	10^{1}	10
one		10^{0}	1
deci	d	10^{-1}	0.1
centi	c	10^{-2}	0.01
milli	m	10^{-3}	0.001
micro	μ	10^{-6}	0.000 001
nano	n	10^{-9}	0.000 000 001
pico	p	10^{-12}	0.000 000 000 001
femto	f	10^{-15}	0.000 000 000 000 001

Ohm's Law $V = IR, \quad I = \frac{V}{R}, \quad R = \frac{V}{I}$

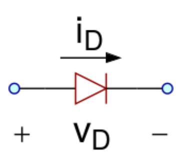
Complex Numbers

- $z = x + iy = re^{i\theta} = r[\cos(\theta) + i\sin(\theta)]$
- $[r(\cos(\theta) + i\sin(\theta))]^n = r^n[\cos(n\theta) + i\sin(n\theta)]$
- $z^n = (re^{i\theta}) = r^n e^{in\theta}$
- $\frac{1}{i} = -i$
- $\sqrt[n]{z} = \sqrt[n]{r}e^{\frac{\theta}{n} + \frac{2k\pi}{n}}$ for $n \in N^*$ (ints ≥ 0)
- $e^{j\theta} = \cos(\theta) + j\sin(\theta)$
- $e^{-j\theta} = \cos(\theta) - j\sin(\theta)$
- $\cos(\theta) = \frac{1}{2}(e^{j\theta} + e^{-j\theta})$
- $\sin(\theta) = \frac{1}{2j}(e^{j\theta} - e^{-j\theta})$
- normalized: $sinc(t) = \frac{\sin(\pi t)}{\pi t}$
- $|\frac{a}{b}| = \frac{|a|}{|b|}$
- $\angle\frac{a}{b} = \angle a - \angle b$

Trig

- $\cos^2(a) + \sin^2(a) = 1$
- $\cos(2a) = \cos^2(a) - \sin^2(a) = 2\cos^2(a) - 1 = 1 - 2\sin^2(a)$
- $\sin(2a) = 2\sin(a)\cos(a)$
- $\cos^2(a) = \frac{1}{2}(1 + \cos(2a))$
- $\sin^2(a) = \frac{1}{2}(1 - \cos(2a))$

Diodes



- ideal:
  - $I_D(V_D < 0) = 0$
  - $I_D(V_D \geq 0) = \infty$
- constant drop model: (just the ideal model shifted right by 0.7V)
  - $I_D(V_D < 0.7) = 0$
  - $I_D(V_D \geq 0.7) = \infty$
- exponential model: $I_D = I_S(e^{\frac{V_D}{nV_T}} - 1)$
  - $I_S = 10^{-12}$A (saturation current)
  - $V_T = 25$mV
- small signal resistance: $R_d = \frac{nV_T}{I_D}$
  - I_D: average (DC) current through diode (due to forward bias)
- bridge rectifier shape: square/diamond with all the diodes point toward the + end of the output (away from ground)
  current goes → from cathode (-) to anode (+)

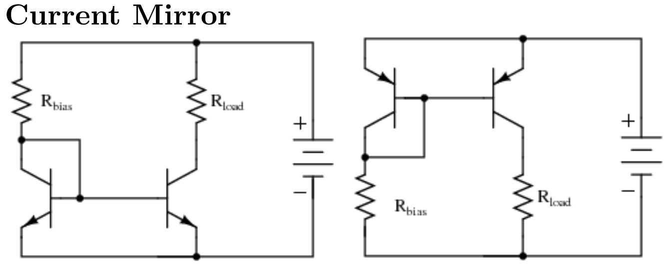
Design an (unregulated) AC adapter

- V_S: AC voltage input
  - standard AC voltage is $110\sqrt{2}V \approx 155.563V$
- V_{S2}: output of transformer (still AC)
- V_p: peak DC output
  - V_r: peak-to-peak ripple voltage (maximum variation)
- $V_p = V_{S2} -$ (diode voltage)
  - diode voltage = 0.7V for single wave rectifier or center-tapped transformer
  - diode voltage = 1.4V for full-wave rectifier
  - (corresponds to how many diodes you need)
- turns ratio $= n = \frac{V_S}{V_{S2}}$
- apparent load resistance: $R_L = \frac{V_o}{I_L}$
- ripple voltage: $V_r = \frac{f}{R_L C}$
  - f: actual ripple frequency (double for full-wave rectifier)
  - C: filter cap size
- Peak Inverse Voltage: $PIV = V_{S2} - 0.7V$
- avg diode current: $I_{Davg} = I_L\left(1 + \pi\sqrt{\frac{2}{V_r}}\right)$
- max diode current: $I_{Dmax} = I_L\left(1 + 2\pi\sqrt{\frac{2}{V_r}}\right)$
  - only difference is $\pi \to 2\pi$

Transistors

- $V_T = 25$mV at room temperature (according to textbook and prof),
  $V_T = 26$mV at room temperature (according to lab)
- β: a physical constant of the transistor. Usually about 100 or 200
- $I_B + I_C = I_E$, $I_C = \beta I_B$, $I_E = (1+\beta)I_B$
- $\alpha = \frac{\beta}{1+\beta}$, $I_C = \alpha I_E$
- $I_C = I_S(e^{\frac{V_{BE}}{nV_T}})$,
- AC (assumes correct DC bias): $g_m = \frac{1}{r_e} = \frac{I_C}{V_T}$

Current Mirror



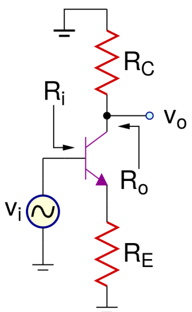
(a) current sinking (b) current-sourcing

- Q1 has the base shorted to collector, Q2 does not
- $R_{bias} = R_{ref}$: the current that is mirrored
- $I_{ref} = (V_{CC} - 0.7)/R_{ref}$
- R_{load} has the same current through it as R_{ref} does
  - that is, $I_{ref} = I_{load}$
- you can chain together multiple transistors (Q3,Q4...) all off of the same Q1 and they will all get the same current
  - In this case, each Q2,Q3... output is considered separate from each other in both DC and AC analysis
- only applies when transistors are matched! (we assume they are)

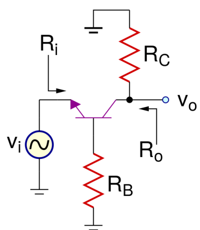
Transistor circuits by inspection

- this all assumes that the transistor is properly DC biased
- three types of amplifier circuits: common emitter, common base, common collector
  - CE, CB, CC
  - the "common" pin is the one that is neither AC input nor output
- intrinsic gain: gain directly from the input pin of the transistor to the output, ignoring any source resistance or such things whatever

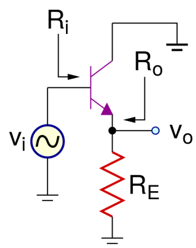
* when you chain multiple amplifiers together, this is the one you use
- when you're driving a finite-impedance load (a load other than open circuit), you have to consider R_o as $R_o||R_L$
  * this will change the gain, which is why it's often helpful to put a CC buffer at the end of an amplifier
- R_i: input impedance: impedance as seen from the input
  * includes the transistor, does not include R_s
- $g_m = \frac{I_C}{V_T}$
  $r_\pi = \frac{beta}{g_m}$
  $r_e = \frac{V_T}{I_E} = \frac{\alpha}{g_m} \approx \frac{1}{g_m}$
  $r_o = \frac{V_A}{I_C} \approx \infty$



Common Emitter (CE)



Common Base (CB)



Common Collector (CC)

- CE: Common Emitter
  * input: base; output: collector
  * intrinsic gain: $\frac{V_o}{V_b} = -\alpha\frac{R_C}{r_e+R_E} \approx -\frac{R_C}{r_e+R_E}$
  * $R_i = (\beta+1)(r_e+R_E)$
  * $R_o = R_C$
  * if you have a R_L then you have to put that in parallel with R_C when calculating $\frac{V_o}{V_b}$
- CB: Common Base
  * $\frac{V_o}{V_b} = \alpha\frac{R_C}{R_i} \approx \frac{R_C}{R_i}$
  * $R_i = r_e + \frac{R_B}{\beta+1}$
  * $R_o = R_C$
- CC: Common Collector
  * gain ≈ 1 because it's a buffer
  * $\frac{V_o}{V_b} = \frac{R_E}{r_e+R_E}$
  * $R_i = (\beta+1)(r_e+R_E)$
  * $R_o = R_E||r_e = \frac{R_E*r_e}{R_E+r_e}$